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## Is Now



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# 2N5460, 2N5461, 2N5462

## JFET Amplifier

### P-Channel – Depletion

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

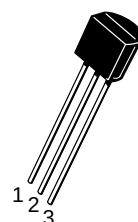
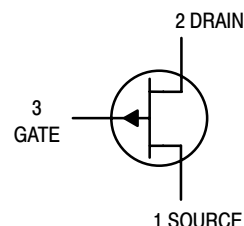
| Rating                                                                                 | Symbol     | Value           | Unit                       |
|----------------------------------------------------------------------------------------|------------|-----------------|----------------------------|
| Drain – Gate Voltage                                                                   | $V_{DG}$   | 40              | Vdc                        |
| Reverse Gate – Source Voltage                                                          | $V_{GSR}$  | 40              | Vdc                        |
| Forward Gate Current                                                                   | $I_{G(f)}$ | 10              | mAdc                       |
| Total Device Dissipation @ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$      | 350<br>2.8      | mW<br>mW/ $^\circ\text{C}$ |
| Junction Temperature Range                                                             | $T_J$      | $-65$ to $+135$ | $^\circ\text{C}$           |
| Storage Channel Temperature Range                                                      | $T_{stg}$  | $-65$ to $+150$ | $^\circ\text{C}$           |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



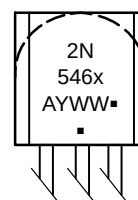
**ON Semiconductor®**

<http://onsemi.com>



**TO-92  
CASE 29  
STYLE 7**

#### MARKING DIAGRAM



2N546x = Device Code

x = 0, 1, or 2

A = Assembly Location

Y = Year

WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N5460, 2N5461, 2N5462

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

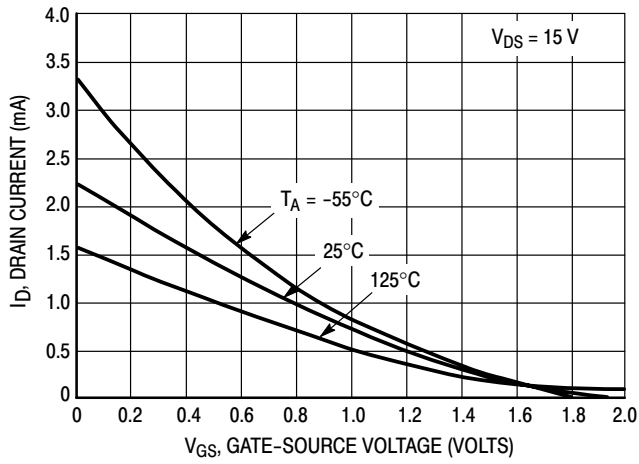
| Characteristic                                                                                                                     | Symbol        | Min                  | Typ         | Max                  | Unit                         |
|------------------------------------------------------------------------------------------------------------------------------------|---------------|----------------------|-------------|----------------------|------------------------------|
| <b>OFF CHARACTERISTICS</b>                                                                                                         |               |                      |             |                      |                              |
| Gate – Source Breakdown Voltage<br>( $I_G = 10\ \mu\text{Adc}$ , $V_{DS} = 0$ )                                                    | $V_{(BR)GSS}$ | 40                   | –           | –                    | Vdc                          |
| Gate Reverse Current<br>( $V_{GS} = 20\ \text{Vdc}$ , $V_{DS} = 0$ )                                                               | $I_{GSS}$     | –                    | –           | 5.0                  | nAdc                         |
| ( $V_{GS} = 30\ \text{Vdc}$ , $V_{DS} = 0$ )                                                                                       |               | –                    | –           | 1.0                  | $\mu\text{Adc}$              |
| ( $V_{GS} = 20\ \text{Vdc}$ , $V_{DS} = 0$ , $T_A = 100^\circ\text{C}$ )                                                           |               | –                    | –           | –                    | –                            |
| ( $V_{GS} = 30\ \text{Vdc}$ , $V_{DS} = 0$ , $T_A = 100^\circ\text{C}$ )                                                           |               | –                    | –           | –                    | –                            |
| Gate – Source Cutoff Voltage<br>( $V_{DS} = 15\ \text{Vdc}$ , $I_D = 1.0\ \mu\text{Adc}$ )                                         | $V_{GS(off)}$ | 0.75<br>1.0<br>1.8   | –<br>–<br>– | 6.0<br>7.5<br>9.0    | Vdc                          |
| Gate – Source Voltage<br>( $V_{DS} = 15\ \text{Vdc}$ , $I_D = 0.1\ \text{mAdc}$ )                                                  | $V_{GS}$      | 0.5                  | –           | 4.0                  | Vdc                          |
| ( $V_{DS} = 15\ \text{Vdc}$ , $I_D = 0.2\ \text{mAdc}$ )                                                                           |               | 0.8                  | –           | 4.5                  |                              |
| ( $V_{DS} = 15\ \text{Vdc}$ , $I_D = 0.4\ \text{mAdc}$ )                                                                           |               | 1.5                  | –           | 6.0                  |                              |
| <b>ON CHARACTERISTICS</b>                                                                                                          |               |                      |             |                      |                              |
| Zero – Gate – Voltage Drain Current<br>( $V_{DS} = 15\ \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0\ \text{kHz}$ )                        | $I_{DSS}$     | –1.0<br>–2.0<br>–4.0 | –<br>–<br>– | –5.0<br>–9.0<br>–16  | mAdc                         |
| <b>SMALL – SIGNAL CHARACTERISTICS</b>                                                                                              |               |                      |             |                      |                              |
| Forward Transfer Admittance<br>( $V_{DS} = 15\ \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0\ \text{kHz}$ )                                | $ y_{fs} $    | 1000<br>1500<br>2000 | –<br>–<br>– | 4000<br>5000<br>6000 | $\mu\text{mhos}$             |
| Output Admittance ( $V_{DS} = 15\ \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0\ \text{kHz}$ )                                             | $ y_{os} $    | –                    | –           | 75                   | $\mu\text{mhos}$             |
| Input Capacitance ( $V_{DS} = 15\ \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0\ \text{MHz}$ )                                             | $C_{iss}$     | –                    | 5.0         | 7.0                  | pF                           |
| Reverse Transfer Capacitance ( $V_{DS} = 15\ \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0\ \text{MHz}$ )                                  | $C_{rss}$     | –                    | 1.0         | 2.0                  | pF                           |
| <b>FUNCTIONAL CHARACTERISTICS</b>                                                                                                  |               |                      |             |                      |                              |
| Equivalent Short – Circuit Input Noise Voltage<br>( $V_{DS} = 15\ \text{Vdc}$ , $V_{GS} = 0$ , $f = 100\ \text{Hz}$ , BW = 1.0 Hz) | $e_n$         | –                    | 60          | 115                  | $\text{nV}/\sqrt{\text{Hz}}$ |

### ORDERING INFORMATION

| Device      | Package            | Shipping†          |
|-------------|--------------------|--------------------|
| 2N5460      | TO-92              | 1000 Units / Box   |
| 2N5460G     | TO-92<br>(Pb-Free) |                    |
| 2N5461      | TO-92              |                    |
| 2N5461G     | TO-92<br>(Pb-Free) |                    |
| 2N5461RLRA  | TO-92              |                    |
| 2N5461RLRAG | TO-92<br>(Pb-Free) | 2000 / Tape & Reel |
| 2N5462      | TO-92              | 1000 Units / Box   |
| 2N5462G     | TO-92<br>(Pb-Free) |                    |

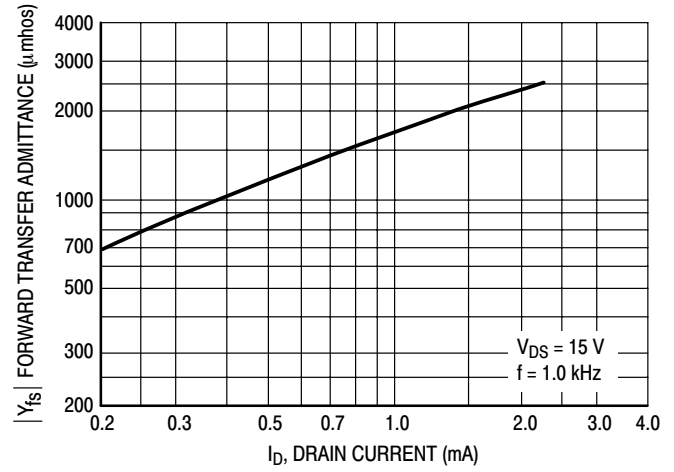
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**DRAIN CURRENT versus GATE  
SOURCE VOLTAGE**

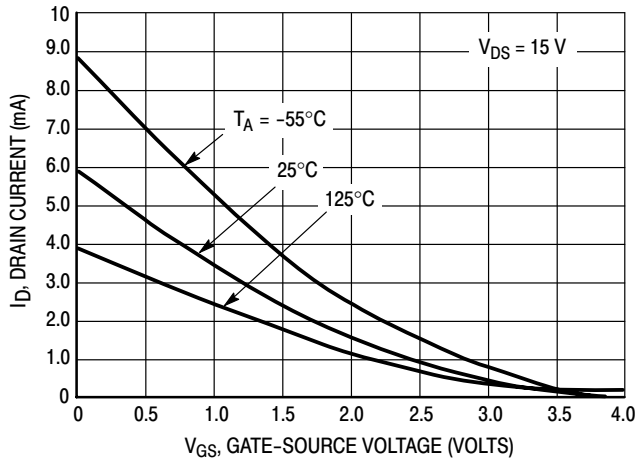


**Figure 1.  $V_{GS(off)} = 2.0$  V**

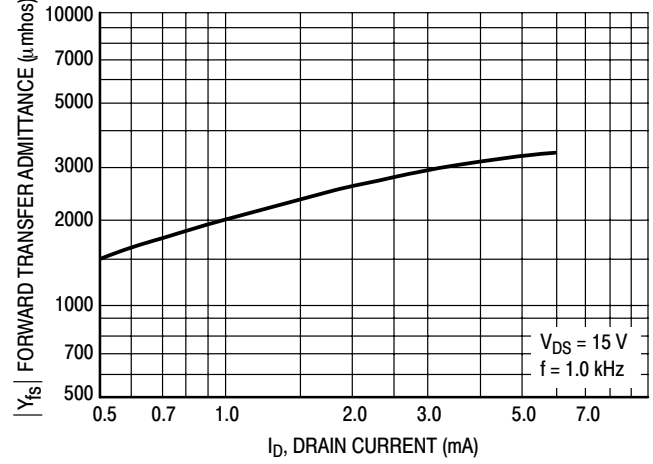
**FORWARD TRANSFER ADMITTANCE  
versus DRAIN CURRENT**



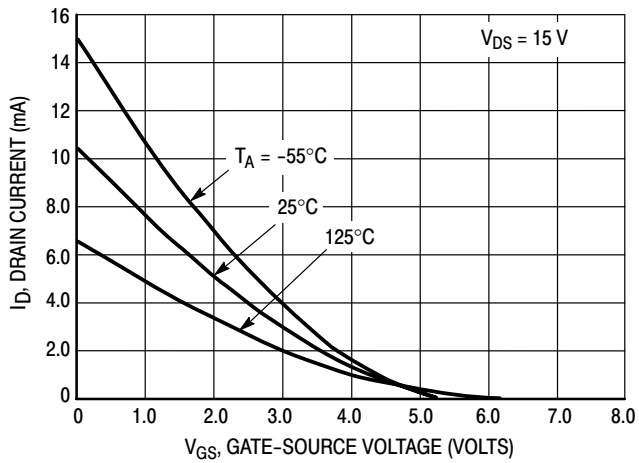
**Figure 4.  $V_{GS(off)} = 2.0$  V**



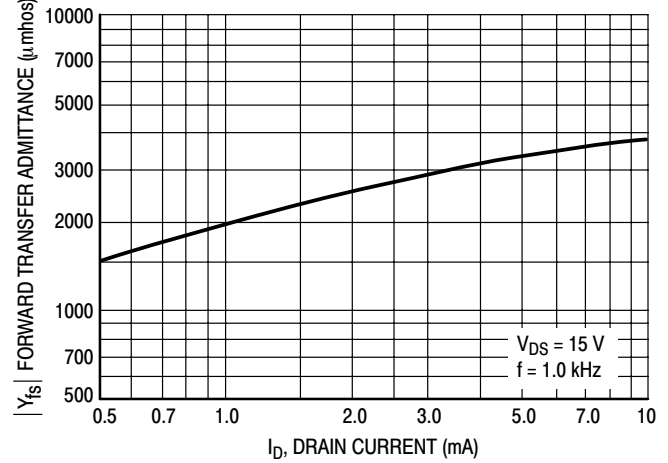
**Figure 2.  $V_{GS(off)} = 4.0$  V**



**Figure 5.  $V_{GS(off)} = 4.0$  V**



**Figure 3.  $V_{GS(off)} = 5.0$  V**



**Figure 6.  $V_{GS(off)} = 5.0$  V**

## 2N5460, 2N5461, 2N5462

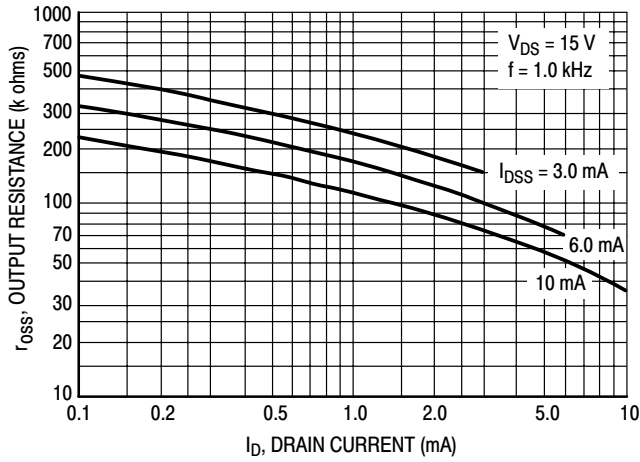


Figure 7. Output Resistance versus Drain Current

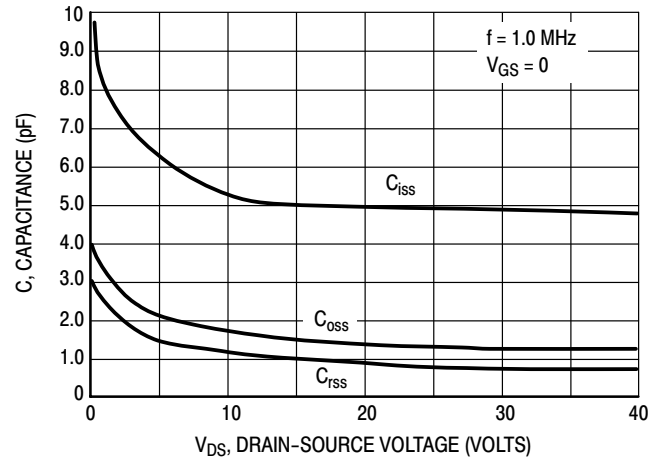


Figure 8. Capacitance versus Drain-Source Voltage

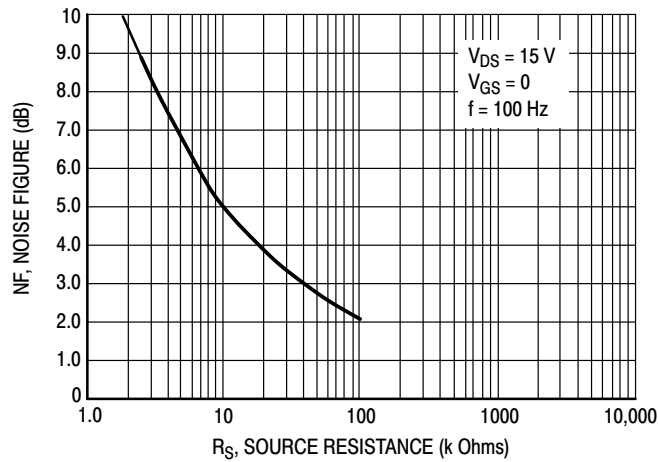
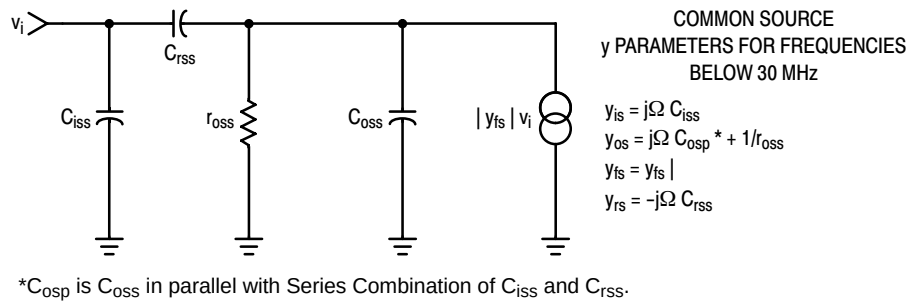


Figure 9. Noise Figure versus Source Resistance



NOTE:

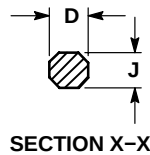
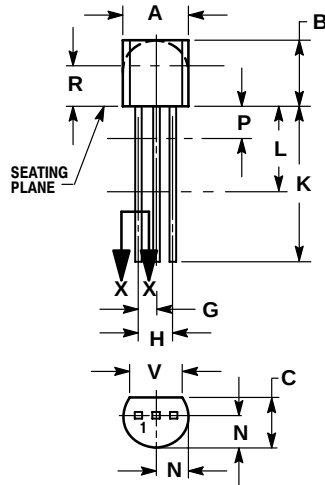
1. Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

Figure 10. Equivalent Low Frequency Circuit

# 2N5460, 2N5461, 2N5462

## PACKAGE DIMENSIONS

TO-92  
CASE 29-11  
ISSUE AL



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.175  | 0.205 | 4.45        | 5.20  |
| B   | 0.170  | 0.210 | 4.32        | 5.33  |
| C   | 0.125  | 0.165 | 3.18        | 4.19  |
| D   | 0.016  | 0.021 | 0.407       | 0.533 |
| G   | 0.045  | 0.055 | 1.15        | 1.39  |
| H   | 0.095  | 0.105 | 2.42        | 2.66  |
| J   | 0.015  | 0.020 | 0.39        | 0.50  |
| K   | 0.500  | ---   | 12.70       | ---   |
| L   | 0.250  | ---   | 6.35        | ---   |
| N   | 0.080  | 0.105 | 2.04        | 2.66  |
| P   | ---    | 0.100 | ---         | 2.54  |
| R   | 0.115  | ---   | 2.93        | ---   |
| V   | 0.135  | ---   | 3.43        | ---   |

### STYLE 7:

1. SOURCE
2. DRAIN
3. GATE

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